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November 2013



FAIRCHILD

FGH75T65UPD_F085 650V, 75A Field Stop Trench IGBT

Features

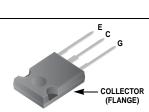
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for easy parallel operating
- High current capability
- Low saturation voltage: $V_{CE(sat)} = 1.65V(Typ.) @ I_C = 75A$
- High input impedance
- Tightened Parameter Distribution
- RoHS compliant
- Qualified to Automotive Requirements of AEC-Q101

General Description

Using Novel Field Stop Trench IGBT Technology, Fairchild's new series of Field Stop Trench IGBTs offer the optimum performance for Automotive chargers, Solar Inverter, UPS and Digital Power Generator where low conduction and switching losses are essential.

Applications

- Automotive chargers, Converters, High Voltage Auxiliaries
- Solar Inverters, UPS, Digital Power Generator



Absolute Maximum Ratings

Symbol	Description		Ratings	Units	
V _{CES}	Collector to Emitter Voltage		650	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
I _C	Collector Current	@ T _C = 25°C	150	A	
·C	Collector Current	@ T _C = 100°C	75	A	
I _{CM (1)}	Pulsed Collector Current		225	A	
I _F	Diode Forward Current	@ T _C = 25°C	75	A	
	Diode Forward Current	@ T _C = 100°C	50	A	
I _{FM(1)}	Pulsed Diode Maximum Forward Curren	t	225	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	375	W	
	Maximum Power Dissipation	@ T _C = 100°C	187	W	
SCWT	Short Circuit Withstand Time	@ T _C = 25 ^o C	5	us	
TJ	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	Ratings	Units	
$R_{\theta JC}(IGBT)_{(2)}$	Thermal Resistance, Junction to Case 0.4		°C/W	
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	0.86	°C/W	
Symbol	Parameter	Тур.	Units	
R _{0JA} Thermal Resistance, Junction to Ambient (PCB Mou		40	°C/W	

Package Marking and Ordering Information

Device Marking Device		Package	Packing Type	Qty per Tube	
FGH75T65UPD	FGH75T65UPD_F085	85 TO-247 Tube		30ea	

For Fairchild's definition of "green" Eco Status, please visit: <u>http://www.fairchildsemi.com/company/green/rohs_green.html</u>.

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units	
Off Charac	teristics						
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	650	-	-	V	
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	-	0.65	-	V/ºC	
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	1	
		I _{CES} at 80%*B _{VCES,} 175°C	-	-	3600	μA	
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA	
On Charac	teristics						
V _{GE(th)}	G-E Threshold Voltage	$I_{C} = 75 \text{mA}, V_{CE} = V_{GE}$	4.0	6.0	7.5	V	
00(01)		$I_{\rm C} = 75$ A, $V_{\rm GE} = 15$ V	-	1.69	2.3	V	
V _{CE(sat)}	Collector to Emitter Saturation Voltage	$I_{C} = 75A, V_{GE} = 15V,$ $T_{C} = 175^{\circ}C$	-	2.21	-	V	
Dynamic C	haracteristics						
C _{ies}	Input Capacitance		-	5665	-	pF	
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,}V_{GE} = 0V_{,}$	-	205	_	pF	
C _{res}	Reverse Transfer Capacitance	f = 1MHz	_	100	-	pF	
	•	I			I		
	Characteristics				10		
t _{d(on)}	Turn-On Delay Time	-	-	32	48	ns	
t _r	Rise Time		-	43	71	ns	
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 V, I_C = 75 A,$	-	166	216	ns	
t _f	Fall Time	$R_G = 3\Omega$, $V_{GE} = 15V$, Inductive Load, $T_C = 25^{\circ}C$	-	24	33	ns	
Eon	Turn-On Switching Loss	-	-	2.85	4.80	mJ	
E _{off}	Turn-Off Switching Loss		-	1.20	1.60	mJ	
E _{ts}	Total Switching Loss		-	4.05	5.3	mJ	
t _{d(on)}	Turn-On Delay Time		-	30	-	ns	
t _r	Rise Time		-	57	-	ns	
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 V, I_C = 75 A,$	-	176	-	ns	
t _f	Fall Time	$R_G = 3\Omega$, $V_{GE} = 15V$,	-	21	-	ns	
Eon	Turn-On Switching Loss	Inductive Load, $T_C = 175^{\circ}C$	-	4.45	-	mJ	
E _{off}	Turn-Off Switching Loss		-	1.60	-	mJ	
E _{ts}	Total Switching Loss]	-	6.05	-	mJ	
Tsc	Short Circuit Withstand Time	$V_{\rm GE}$ = 15V, $V_{\rm CC} \le 400$ V, Rg = 10 Ω	5	-	-	us	

Notes:

1:Repetitive rating: Pulse width limited by max junction temperature.

2:Rthjc for TO-247 : according to Mil standard 883-1012 test method. Rthja for TO-247 : according to JESD51-2, test method environmental condition and JESD51-10, test boards for through hole perimeter leaded package thermal measurements. JESD51-3 : Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Package.

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Electrical Characteristics of the IGBT (Continued)

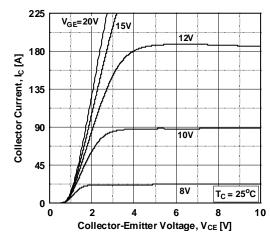
Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Units
Qg	Total Gate Charge		-	385	578	nC
Q _{ge}	Gate to Emitter Charge	V _{CE} = 400V, I _C = 75A, V _{GE} = 15V	-	45	68	nC
Q _{gc}	Gate to Collector Charge	VGE - 10V	-	210	315	nC

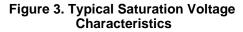
Electrical Characteristics of the Diode $T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Мах	Units
V _{FM}	Diode Forward Voltage	$I_F = 50A$	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	2.1	2.6	V
* FIVI			T _C = 175 ^o C	-	1.7	-	
E _{rec}	Reverse Recovery Energy		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	40	-	uJ
t	Diode Reverse Recovery Time	I _F =50A, dI _F /dt = 200A/μs	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	43	85	ns
۲r		$1F = 30A$, $0F/0t = 200A/\mu s$	T _C = 175 ^o C	-	162	-	110
Q _{rr}	Diode Reverse Recovery Charge		$T_{\rm C} = 25^{\rm o}{\rm C}$	-	83	170	nC
~11	2.000 Hororor Hororory Charge		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	805	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics





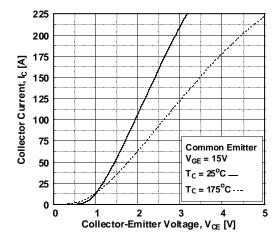


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

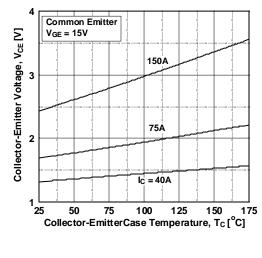


Figure 2. Typical Output Characteristics

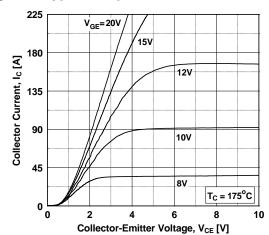
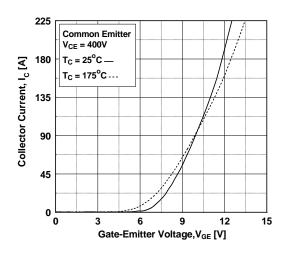
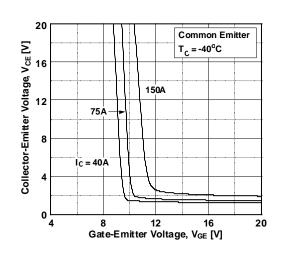


Figure 4. Transfer Characteristics

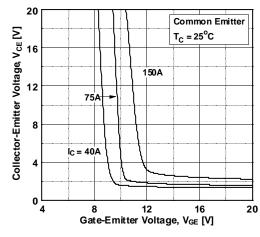






Typical Performance Characteristics







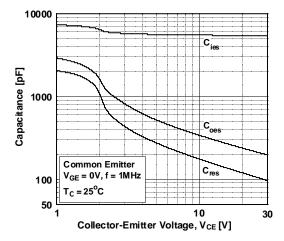


Figure 11. SOA Characteristics

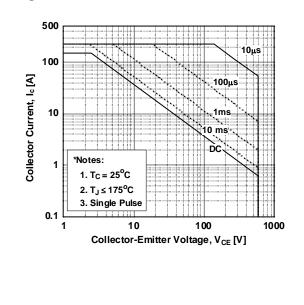


Figure 8. Saturation Voltage vs. V_{GE}

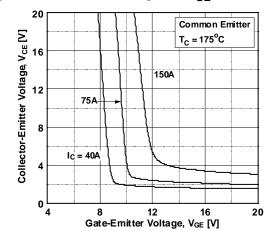


Figure 10. Gate charge Characteristics

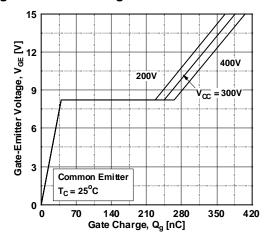
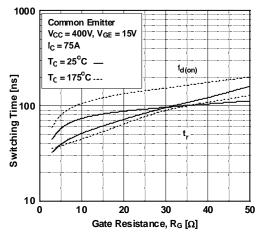
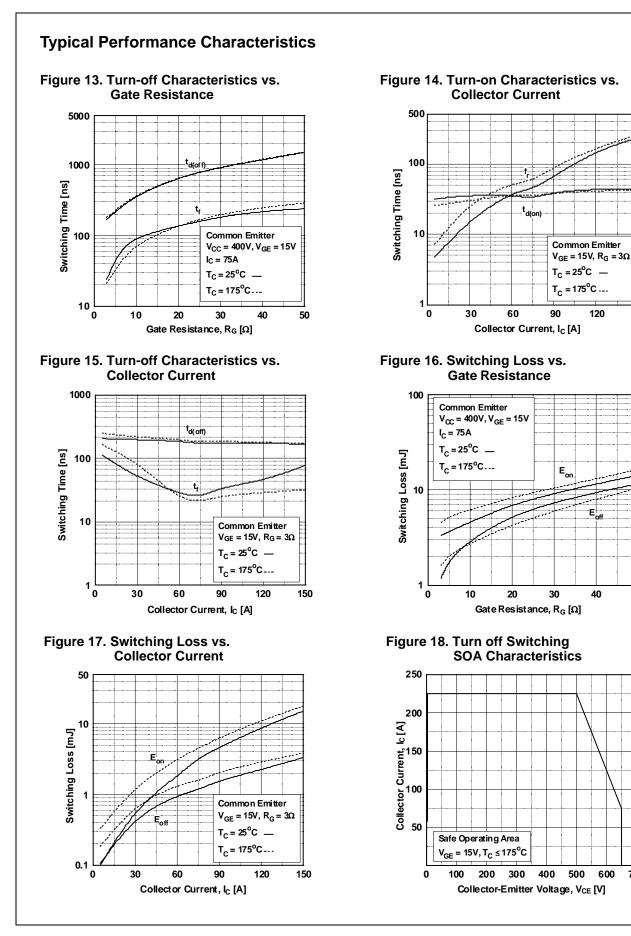


Figure 12. Turn-on Characteristics vs. Gate Resistance

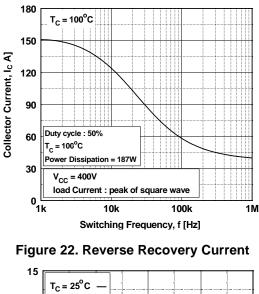


FGH75T65UPD_F085 650V 75A Field Stop IGBT



Typical Performance Characteristics Figure 19. Current Derating 180 Average Forward Current, I_{F(AV)} [A] 150 120 90 60 30 0 175 0 25 50 75 100 125 150 200 Case temperature, T_c [°C] **Figure 21. Forward Characteristics** 300 100 Forward Current, IF [A] T_C = 175°C 10 $T_C = 125^{\circ}C$ T_C = 75°C $T_C = 25^{\circ}C$ 1 1 2 3 Forward Voltage, V_F [V] 0 4 Figure 23. Stored Charge 1.0 = 25°C Stored Recovery Charge, Qrr [uC] 200A/µs = 175°C 0.8 c di/dt = 100A/µs 0.6 0.4

Figure 20. Load Current Vs. Frequence



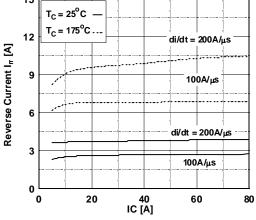
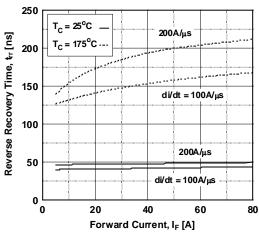


Figure 24. Reverse Recovery Time



0.2

0.0

0

200 A / µs

40

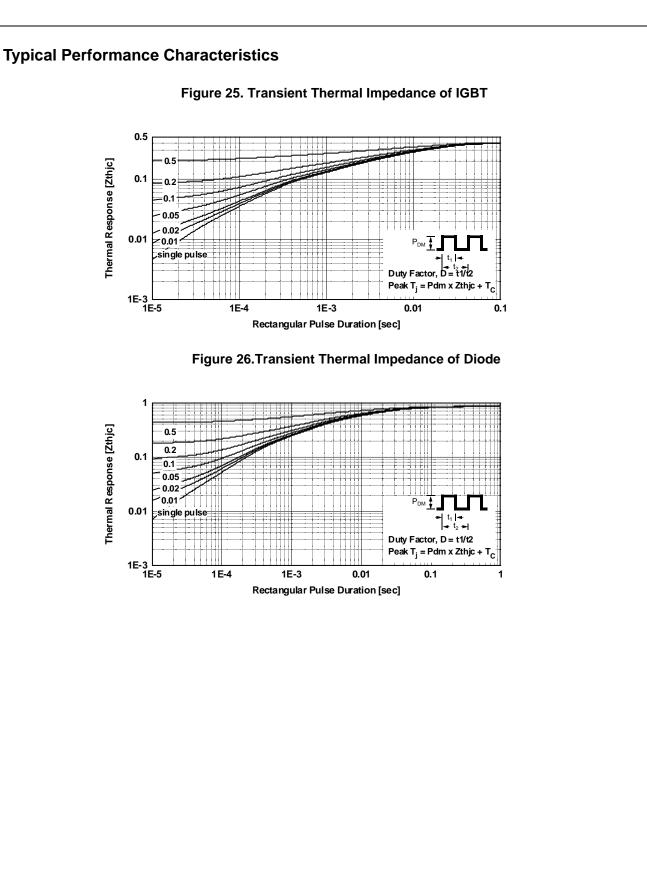
Forwad Current, IF [A]

20

di/dt = 100A/µs

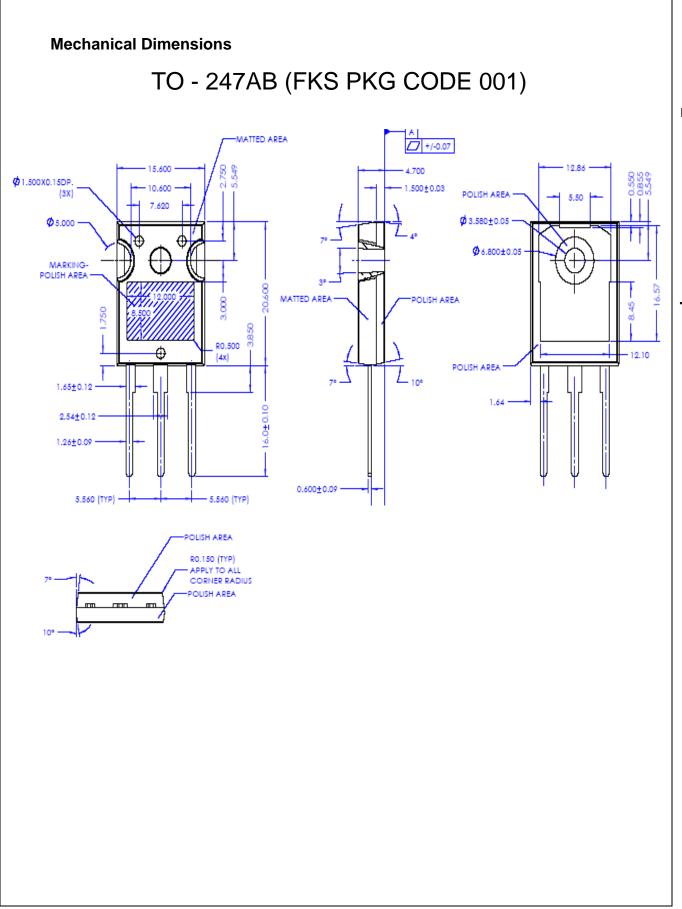
80

60



Thermal Response [Zthjc]

Thermal R esponse [Zthjc]





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